

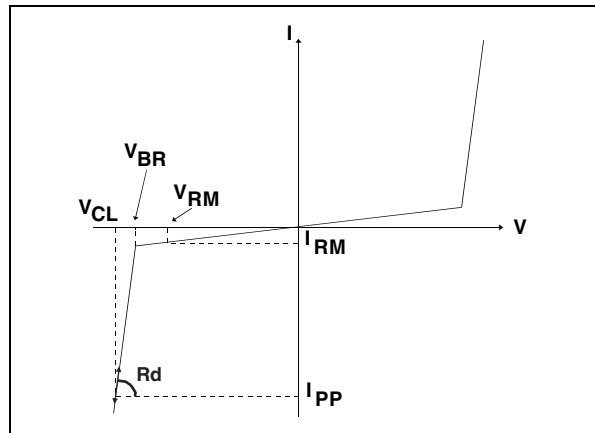
**Table 2: Absolute Maximum Ratings** ( $T_{amb} = 25^{\circ}\text{C}$ )

Symbol	Parameter		Value	Unit
$V_{PP}$	ESD discharge	MIL STD 883C - Method 3015-6 IEC61000-4-2 air discharge IEC61000-4-2 contact discharge	25 15 8	kV
$P_{PP}$	Peak pulse power (8/20 $\mu\text{s}$ )		80	W
$T_j$	Junction temperature		150	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature range		-55 to +150	$^{\circ}\text{C}$
$T_L$	Maximum lead temperature for soldering during 10 s at 5mm for case		260	$^{\circ}\text{C}$
$T_{op}$	Operating temperature range (note 1)		-40 to +125	$^{\circ}\text{C}$

**Note 1:** Variation of parameters is given by curves.

**Table 3: Electrical Characteristics** ( $T_{amb} = 25^{\circ}\text{C}$ )

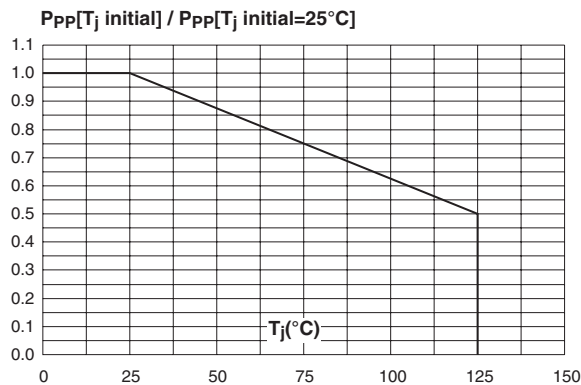
Symbol	Parameter
$V_{RM}$	Stand-off voltage
$V_{BR}$	Breakdown voltage
$V_{CL}$	Clamping voltage
$I_{RM}$	Leakage current
$I_{PP}$	Peak pulse current
$\alpha T$	Voltage temperature coefficient
$V_F$	Forward voltage drop
$C$	Capacitance
$R_d$	Dynamic resistance



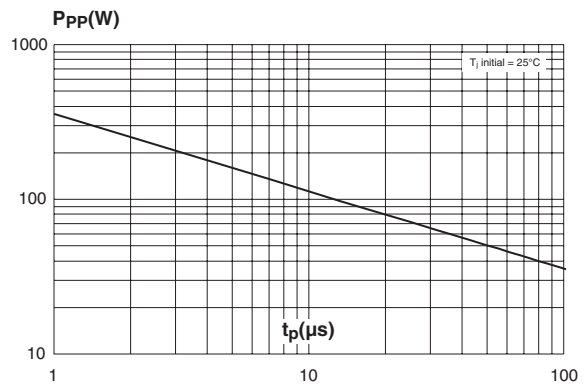
Type	$V_{BR}$ @		$I_R$	$I_{RM}$ @ $V_{RM}$		$R_d$ typ. note 2	$\alpha T$ max.	$C$ typ. 0V bias
	min.	max.		max.				
	V	V		$\mu\text{A}$	V	$\Omega$	$10^{-4}/^{\circ}\text{C}$	pF
ESDA6V1-4BC6	6.1	8	1	1	3	0.45	3	45

**Note 2:** Square pulse,  $I_{PP} = 3\text{A}$ ,  $t_p = 2.5\mu\text{s}$ .

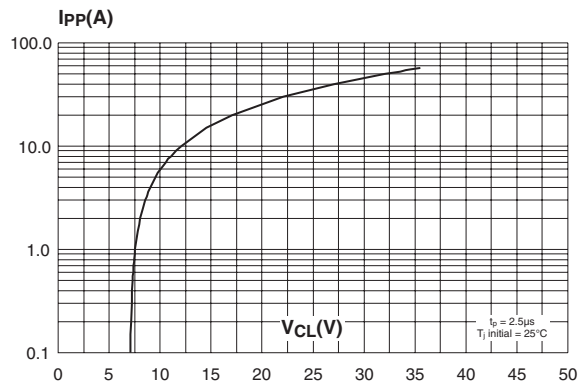
**Figure 2: Relative variation of peak pulse power versus initial junction temperature**



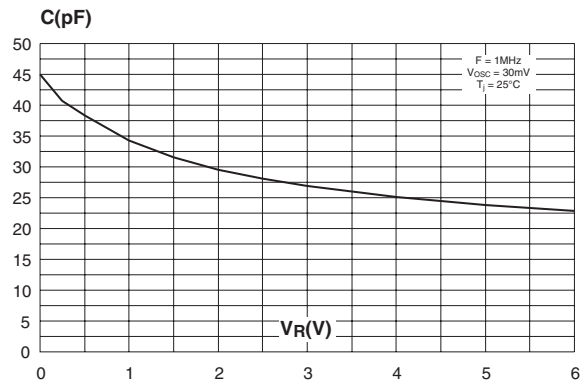
**Figure 3: Peak pulse power versus exponential pulse duration**



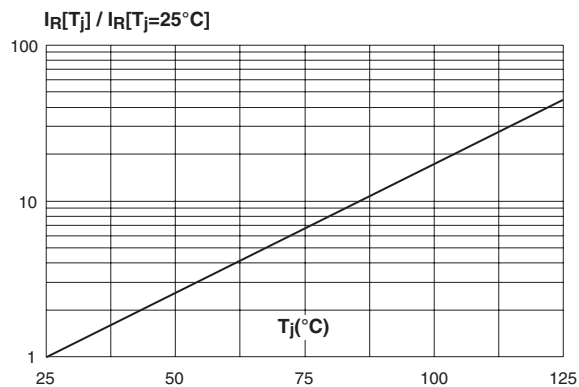
**Figure 4: Clamping voltage versus peak pulse current (typical values, rectangular waveform)**



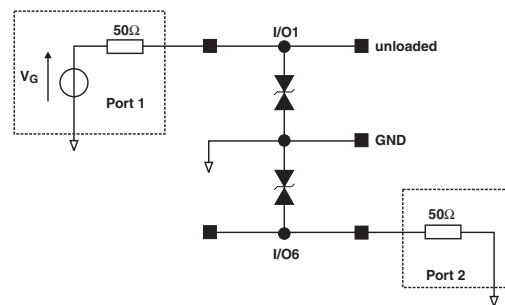
**Figure 5: Junction capacitance versus line voltage applied (typical values)**



**Figure 6: Relative variation of leakage current versus junction temperature (typical values)**



**Figure 7: Analog crosstalk test configuration**



## 1. ESD protection by ESDA6V1-4BC6

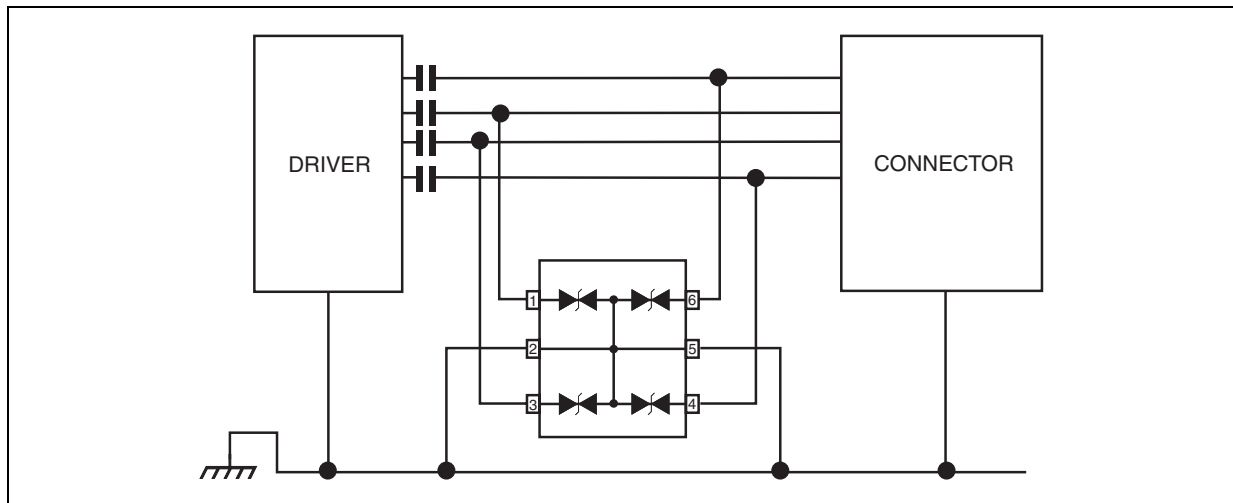
With the focus of lowering the operation levels, the problem of malfunction caused by the environment is critical. Electrostatic discharge (ESD) is a major cause of failure in electronic system.

Transient Voltage Suppressors are an ideal choice for ESD protection and have proven capable in suppressing ESD events. They are capable of clamping the incoming transient to a low enough level such that damage to the protected semiconductor is prevented.

Surface mount TVS arrays offer the best choice for minimal lead inductance.

They serve as parallel protection elements, connected between the signal line to ground. As the transient rises above the operating voltage of the device, the TVS array becomes a low impedance path diverting the transient current to ground.

**Figure 8: Bidirectional protection for 0V biased signals**



The ESDA6V1-4BC6 array is the ideal product for use as board level protection of ESD sensitive semiconductor components.

The tiny SOT23-6L package allows design flexibility in the design of “crowded” boards where the space saving is at a premium. This enables to shorten the routing and can contribute to improve ESD performance.

## 2. Circuit Board Layout

Circuit board layout is a critical design step in the suppression of ESD induced transients. The following guidelines are recommended :

- The ESDA6V1-4BC6 should be placed as near as possible to the input terminals or connectors.
- Minimise the path length between the ESD suppressor and the protected device
- Minimise all conductive loops, including power and ground loops
- The ESD transient return path to ground should be kept as short as possible.
- Use ground planes whenever possible.

**Figure 9: Ordering information scheme**

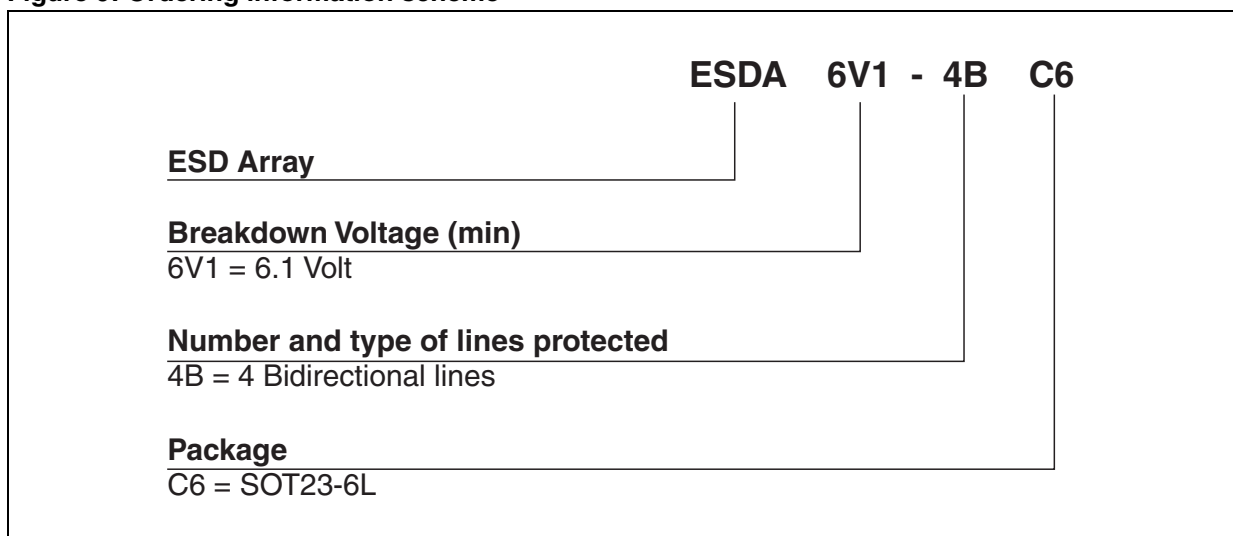


Figure 10: SOT23-6L Package Mechanical Data

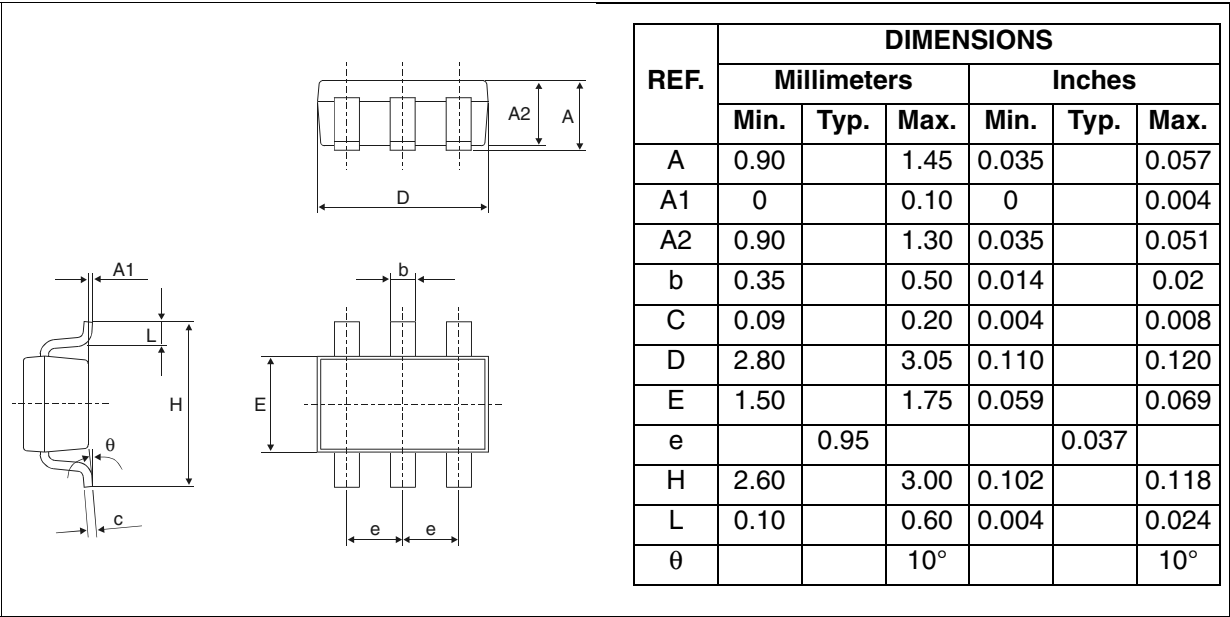


Figure 11: Foot Print Dimensions (in millimeters)

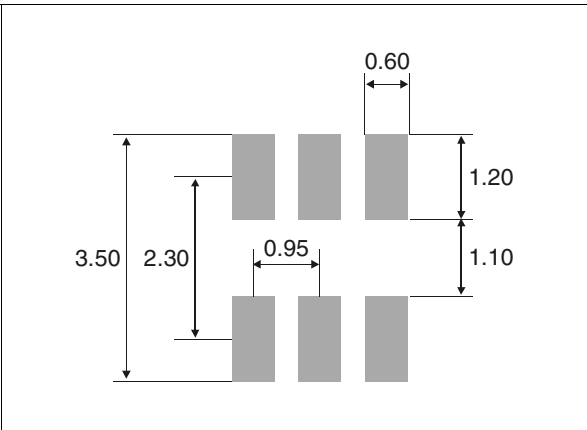


Table 4: Ordering Information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
ESDA6V1-4BC6	BS77	SOT23-6L	16.7 mg	3000	Tape & reel

Table 5: Revision History

Date	Revision	Description of Changes
Nov-2002	1A	First issue.
4-Nov-2004	2	SOT23-6L package dimensions change for reference “D” from 3.0 millimeters (0.118 inches) to 3.05 millimeters (0.120 inches).

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